



NANOSIL

Silicon-based nanostructures and nanodevices for long term nanoelectronics applications

Network of Excellence

WP 5 “Integration and spreading of excellence”

Deliverable 5.4 “Draft of multi-chapter multi-authors book.”

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Deliverable Summary

This deliverable summarizes in few lines the progress/steps done in 2008-2010 to prepare the book focusing on novel materials for ultimate CMOS, advanced modeling & simulation for nano-MOSFETs and nano-characterization methods.

The idea was to highlight in this book the main research advances in the fields for which our Academic and Scientific Community has a great expertise.

Table of contents is also given.

1. Multi-chapter multi-authors book

1.1. Generalities

Discussion on the content and potential contributors of the book was started at the end of 2008 and the contributions were finalized in 2010. The book addresses WP1, WP2, WP3 and WP4 of Nanosil. The book was proposed to contain three parts: i) novel materials; ii) simulations and modeling for nanoscale devices; iii) nanocharacterization methods. Each of these parts consists then in chapters. The length of each chapter was proposed to be about 30 pages, which leads to a book of about 650 pages.

ISTE-Wiley was selected as future Publisher.

Detailed guidelines for the chapters' preparation as well as template given by the Publisher were sent to all contributors in 2009.

At the beginning of 2010, the Copyright agreements were transferred to the Publisher.

Proofs were sent to authors in April 2010.

Finally, the book was published mid- 2010.

<http://www.iste.co.uk/index.php?f=a&ACTION=View&id=357>

Complete reference is:

“Nanoscale CMOS: Innovative Materials, Modeling and Characterization”

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“Hard copy” was sent to a representative of each laboratory contributing to the book.

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